

**Amendments to the claims****Claims 1-20 (canceled)****Claim 21 (previously amended): A method for making a semiconductor device comprising:**

forming on a substrate a high-k gate dielectric layer that comprises a material selected from the group consisting of hafnium oxide, lanthanum oxide, zirconium oxide, zirconium silicon oxide, titanium oxide, tantalum oxide, barium strontium titanium oxide, barium titanium oxide, strontium titanium oxide, yttrium oxide, aluminum oxide, lead scandium tantalum oxide, and lead zinc niobate;

forming a sacrificial layer on the high-k gate dielectric layer;

removing the sacrificial layer; and then

forming a gate electrode that comprises polysilicon on the high-k gate dielectric layer.

**Claims 22-37 (canceled)****Claim 38 (previously amended): The method of claim 21 wherein the gate electrode that comprises polysilicon is formed directly on the high-k gate dielectric layer.**